

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	9122	(laser (light adj emitting adj diode)) and driver and (superstrate cover)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/07 15:16
2	BRS	L2	503	1 and (silicon adj substrate)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/07 15:10
3	BRS	L3	79	2 and hybrid	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/07 15:10
4	BRS	L4	0	((laser (light adj emitting adj diode)) adj array) and (handle adj substrate)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/07 15:17
5	BRS	L5	35	((laser (light adj emitting adj diode))) and (handle adj substrate)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/07 15:17

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	96	(handle adj wafer) and laser	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/07 10:05
2	BRS	L4	2048	257/773-778.ccls. and via	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/07 10:45
3	BRS	L5	96	4 and interposer	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/07 11:08
4	BRS	L6	586	(372/43-50.ccls. 257/80-103.ccls.) and array and (carrier)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/07 11:45
5	BRS	L7	162	(372/43-50.ccls. 257/80-103.ccls.) and array and modulator	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/07 12:27
6	BRS	L8	5468	(372/43-50.ccls. 257/80-103.ccls.) and (singulate cut separate groove channel trench)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/07 11:53

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L9	1264	8 and array	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/07 11:54
8	BRS	L10	359	(372/43-50.ccls. 257/80-103.ccls.) and hybrid	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/07 12:28